

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$ $T_A = 25^\circ C$
30V	4.2Ω @ $V_{GS} = 5V$	200mA
	2.8Ω @ $V_{GS} = 10V$	260mA

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.


## Applications

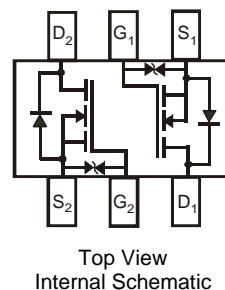
- DC-DC Converters
- Power management functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

## Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)

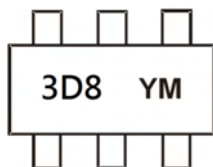


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN63D8LV-7	SOT563	3,000/Tape & Reel
DMN63D8LV-13	SOT563	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com>.

## Marking Information



3D8 = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: Z = 2012)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic				Symbol	Value	Units
Drain-Source Voltage				V <sub>DSS</sub>	30	V
Gate-Source Voltage				V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	I <sub>D</sub>	260 200	mA
Continuous Drain Current (Note 5)	V <sub>GS</sub> = 5V	Steady State	T <sub>A</sub> = 25°C T <sub>A</sub> = 70°C	I <sub>D</sub>	220 160	mA
Pulsed Drain Current (10μs pulse, duty cycle = 1%)				I <sub>DM</sub>	800	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P <sub>D</sub>	450	mW
Thermal Resistance, Junction to Ambient	(Note 5)	R <sub>θJA</sub>	281	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	μA	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10.0	μA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.8	—	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	2.8	Ω	V <sub>GS</sub> = 10.0V, I <sub>D</sub> = 250mA
		—	—	3.8		V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 250mA
		—	—	4.2		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 250mA
		—	—	4.5		V <sub>GS</sub> = 4.0V, I <sub>D</sub> = 250mA
		—	—	13		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 10mA
Forward Transconductance	g <sub>FS</sub>	80	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A
Diode Forward Voltage	V <sub>SD</sub>	-	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	22.0	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	3.2	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	2.0	—		
Gate Resistance	R <sub>G</sub>	—	79.9	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge V <sub>GS</sub> = 10V	Q <sub>g</sub>	—	0.87	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V, I <sub>D</sub> = 150mA
Total Gate Charge V <sub>GS</sub> = 4.5V	Q <sub>g</sub>	—	0.43	—		
Gate-Source Charge	Q <sub>gs</sub>	—	0.11	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	0.11	—	nS	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.115A, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-On Delay Time	t <sub>D(on)</sub>	—	3.3	—		
Turn-On Rise Time	t <sub>r</sub>	—	3.2	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	12.0	—		
Turn-Off Fall Time	t <sub>f</sub>	—	6.3	—		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.  
6. Short duration pulse test used to minimize self-heating effect.  
7. Guaranteed by design. Not subject to production testing.

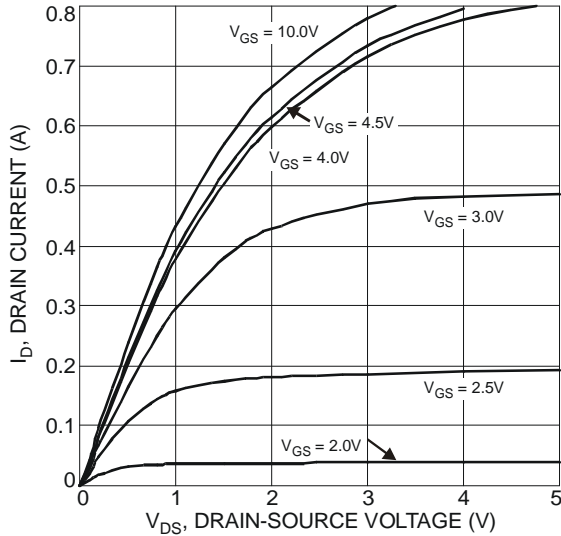


Figure 1 Typical Output Characteristic

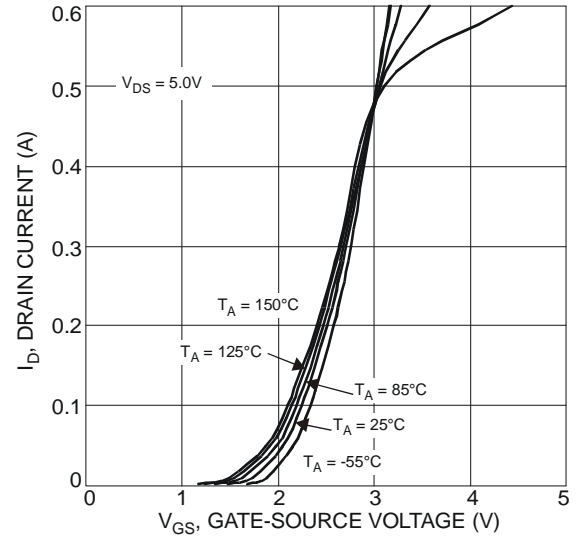


Figure 2 Typical Transfer Characteristics

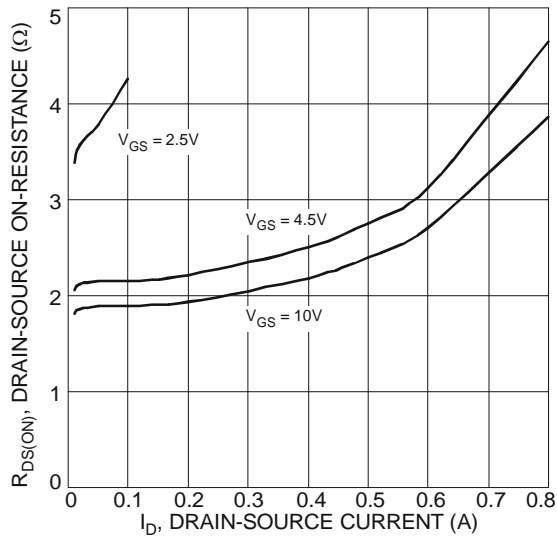


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

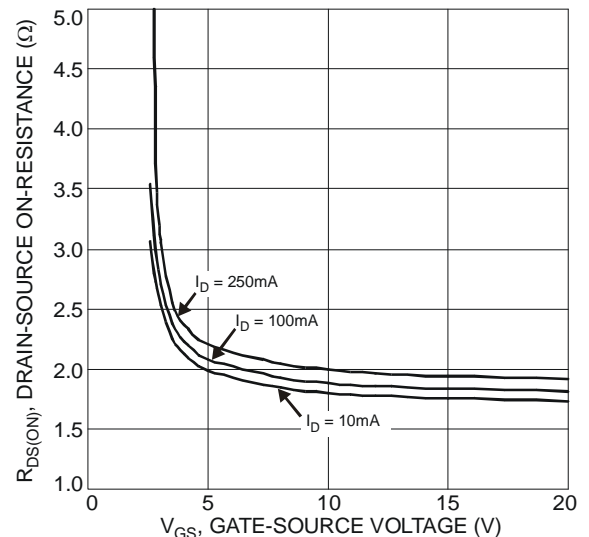


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

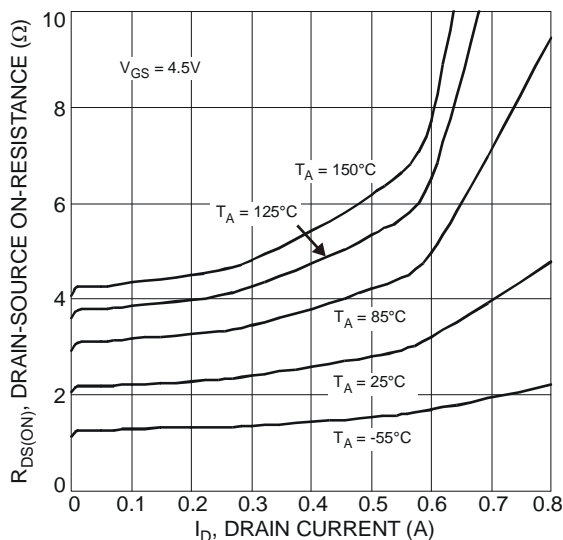


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

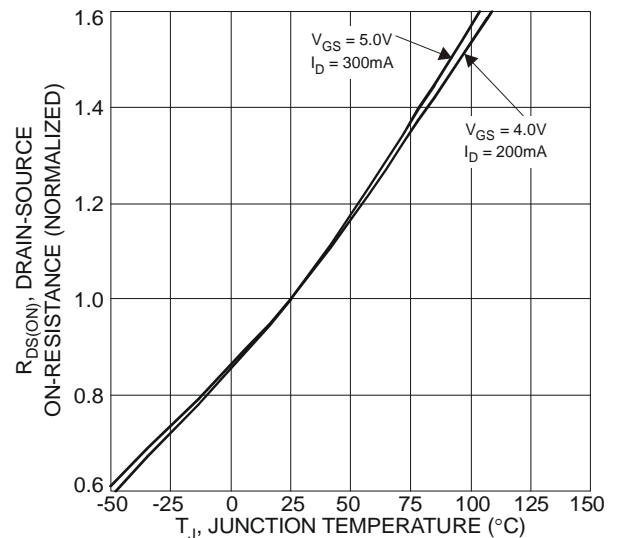


Figure 6 On-Resistance Variation with Temperature

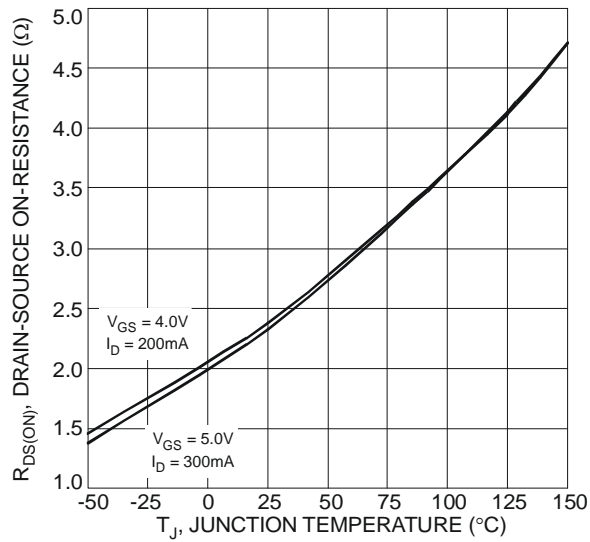


Figure 7 On-Resistance Variation with Temperature

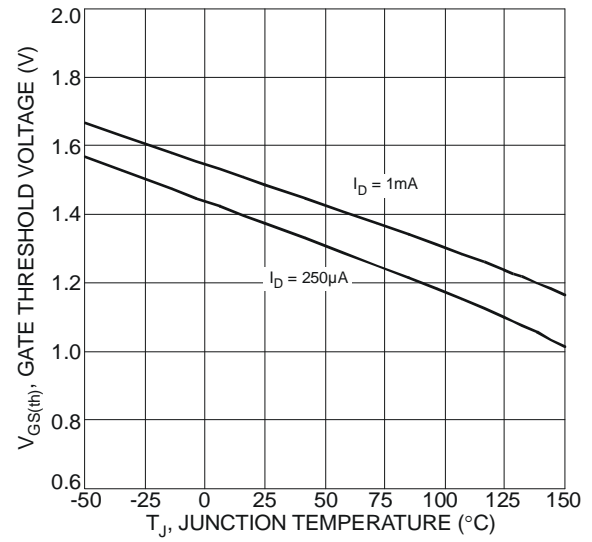


Figure 8 Gate Threshold Variation vs. Ambient Temperature

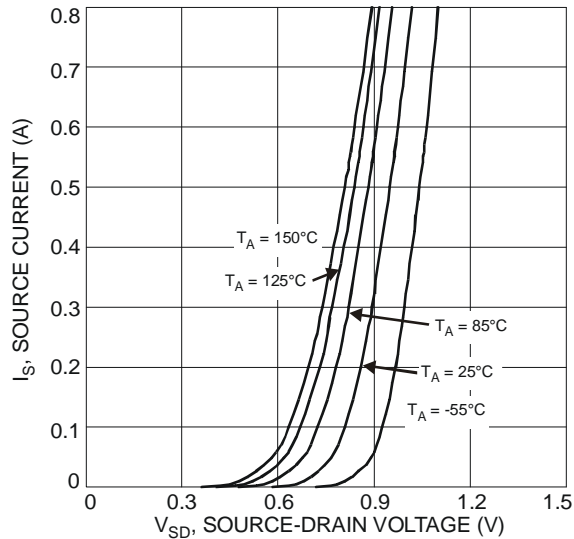
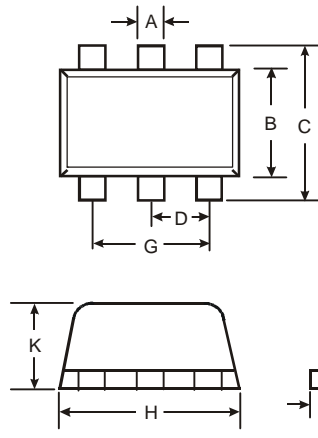


Figure 9 Diode Forward Voltage vs. Current

## Package Outline Dimensions

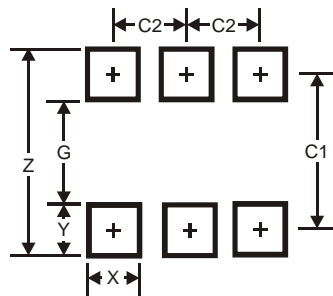
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT563			
Dim	Min	Max	Typ
A	0.15	0.30	0.20
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	-	-	0.50
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.55	0.60	0.60
L	0.10	0.30	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5

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